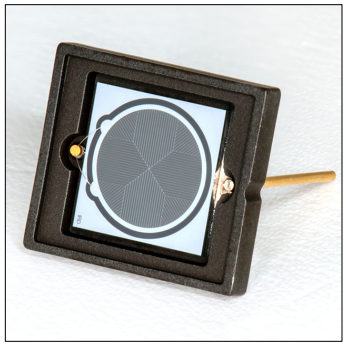
Photodiode Φ5 mm

SXUV20HS1



FEATURES

- Circular Active Area
- Ideal for EUV Detection
- High Speed
- Grid lines 5 microns, Pitch 100 microns
- Superior Radiation Hardness
- High Photon Flux Robustness
- TO-8 package
- Protective Cover Plate[3]

Electro-Optical Characteristics at 25 °C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	Φ5.01 mm		20		mm^2
Responsivity	(see graph on next page)				A/W
Reverse Breakdown Voltage, V_R	I_R = 1 µA	160			Volts
Capacitance, C	V_R = 0 V		200	800	pF
Rise Time	R_L = 50 Ω, V_R = 150 V			3.5	nsec
Dark Current	V_R = 150 V			100	nA

Thermal Parameters

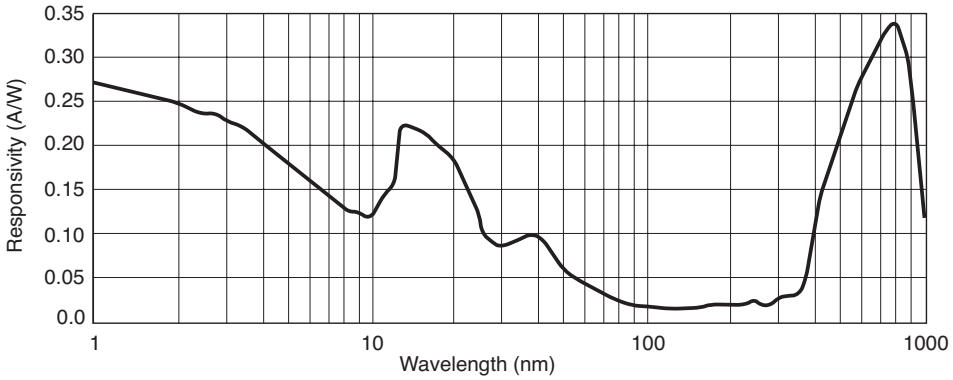
Storage and Operating Temperature Range	Units
Ambient[1]	-10 ° to 40 °C
Nitrogen or Vacuum	-20 °C to 80 °C
Lead Soldering Temperature[2]	260 °C

[1] Temperatures exceeding these parameters may create oxide growth on the active area.
Over time responsivity to low energy radiation and wavelengths below 150 nm will be compromised.

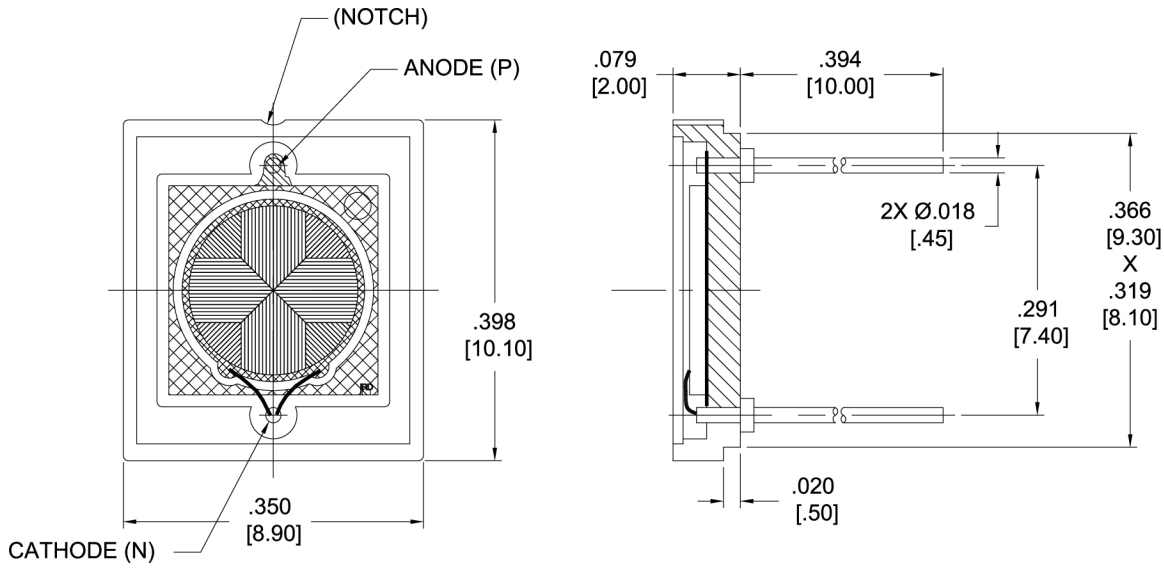
[2] 0.080" from case for 10 seconds.

[3] Shipped with temporary cover to protect the photodiode array and wire bonds.
Review the Application Note, “Handling Precautions for AXUV, SXUV, and UVG Detectors”, prior to removing cover.

Typical Photon Responsivity



Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.